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(54) **DISPLAY APPARATUS HAVING AN OXIDE SEMICONDUCTOR**

(52) **U.S. Cl.**

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(57)

**ABSTRACT**

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A display apparatus include a driving thin film transistor electrically connected to a light-emitting device on each pixel area. The driving thin film transistor may include a driving semiconductor pattern. The driving semiconductor pattern may include an oxide semiconductor. The driving semiconductor pattern may be surrounded by an insulating layer made of fluorinated silicon nitride (SiNF). Thus, in the display apparatus, inflow of hydrogen and oxygen in direction of the driving thin film transistor may be prevented. Therefore, in the display apparatus, changes in characteristics of the driving thin film transistor due to the inflow of the hydrogen and oxygen can be prevented. Accordingly, decrease in the quality of the image in the display apparatus due to the hydrogen and oxygen can be prevented.

